

N and P-Channel Enhancement Mode Power MOSFET

Description

The NCE609 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The complementary MOSFETs may be used to form a level shifted high side switch, and for a host of other applications.

General Features

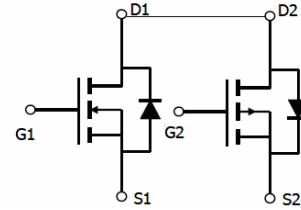
● N-Channel

$V_{DS} = 40V, I_D = 21A$
 $R_{DS(ON)} < 19m\Omega @ V_{GS}=10V$
 $R_{DS(ON)} < 29m\Omega @ V_{GS}=4.5V$

● P-Channel

$V_{DS} = -40V, I_D = -14A$
 $R_{DS(ON)} < 35m\Omega @ V_{GS}=-10V$
 $R_{DS(ON)} < 45m\Omega @ V_{GS}=-4.5V$

- High power and current handling capability
- Lead free product is acquired
- Surface mount package



Schematic diagram



Marking and pin assignment

100% UIS TESTED!

100% ΔV_{ds} TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE609	NCE609	TO-252-4L	-	-	-

Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage	V_{DS}	40	-40	V
Gate-Source Voltage	V_{GS}	± 20	± 20	V
Continuous Drain Current	I_D	$T_A=25^\circ C$	21	-14
		$T_A=70^\circ C$	17.5	-11.5
Pulsed Drain Current ^(Note 1)	I_{DM}	40	-40	A
Maximum Power Dissipation	P_D	40	40	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	-55 To 150	$^\circ C$

Thermal Characteristic

Thermal Resistance, Junction-to-Case ^(Note2)	$R_{\theta JC}$	N-Ch	3.1	$^\circ C/W$
Thermal Resistance, Junction-to-Case ^(Note2)	$R_{\theta JC}$	P-Ch	3.1	$^\circ C/W$

N-CH Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	40	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1	1.5	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =10A	-	14	19	mΩ
		V _{GS} =4.5V, I _D =5A	-	19	29	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =10A		15	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{iss}	V _{DS} =20V, V _{GS} =0V, F=1.0MHz	-	1500	-	PF
Output Capacitance	C _{oss}		-	215	-	PF
Reverse Transfer Capacitance	C _{rss}		-	135	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =20V, R _L =2Ω V _{GS} =10V, R _{GEN} =3Ω	-	4	-	nS
Turn-on Rise Time	t _r		-	11.5	-	nS
Turn-Off Delay Time	t _{d(off)}		-	18	-	nS
Turn-Off Fall Time	t _f		-	5.6	-	nS
Total Gate Charge	Q _g	V _{DS} =20V, I _D =10A, V _{GS} =10V	-	24	-	nC
Gate-Source Charge	Q _{gs}		-	4	-	nC
Gate-Drain Charge	Q _{gd}		-	3.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V, I _S =10A	-	0.8	1.2	V

P-CH Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=-250\mu A$	-40	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-40V, V_{GS}=0V$	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=-10V, I_D=-7A$	-	29	35	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	-	34	45	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=-5V, I_D=-7A$	-	15	-	S
Dynamic Characteristics (Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=-20V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	1225	-	PF
Output Capacitance	C_{oss}		-	190	-	PF
Reverse Transfer Capacitance	C_{rss}		-	120	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=-20V, R_L=2.3\Omega$ $V_{GS}=-10V, R_{GEN}=6\Omega$	-	10	-	nS
Turn-on Rise Time	t_r		-	15	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	30	-	nS
Turn-Off Fall Time	t_f		-	18	-	nS
Total Gate Charge	Q_g	$V_{DS}=-20V, I_D=-7A$ $V_{GS}=-10V$	-	21	-	nC
Gate-Source Charge	Q_{gs}		-	3.5	-	nC
Gate-Drain Charge	Q_{gd}		-	3.0	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	$V_{GS}=0V, I_S=-14A$	-	-	-1.2	V

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production

N- Channel Typical Electrical and Thermal Characteristics (Curves)

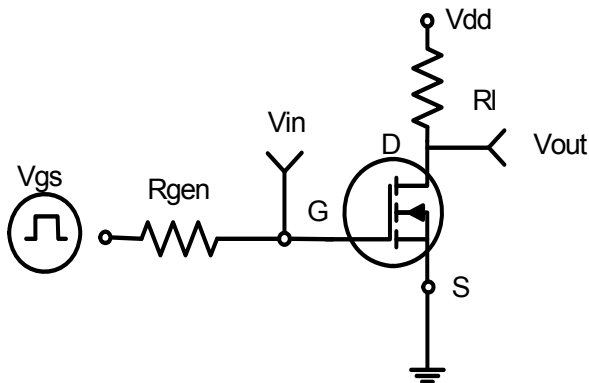


Figure 1: Switching Test Circuit

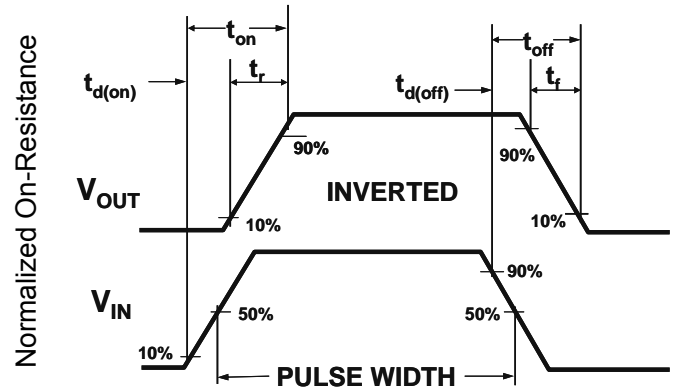


Figure 2: Switching Waveforms

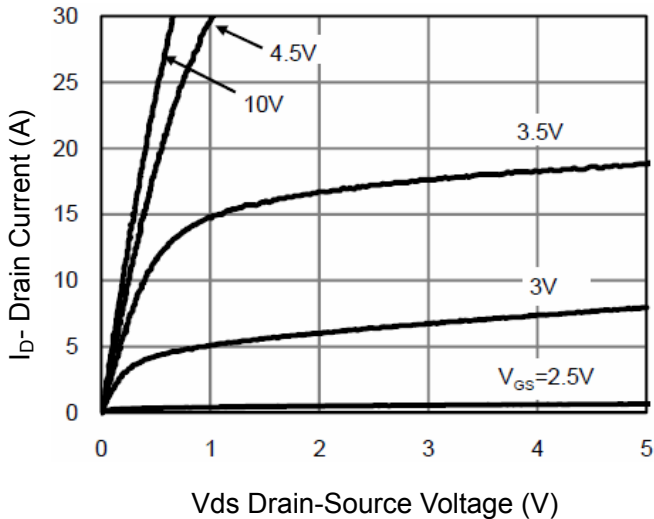


Figure 3 Output Characteristics

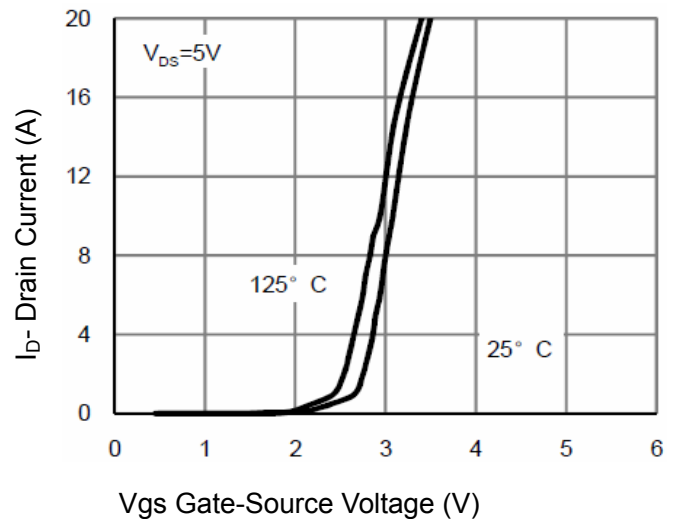


Figure 4 Transfer Characteristics

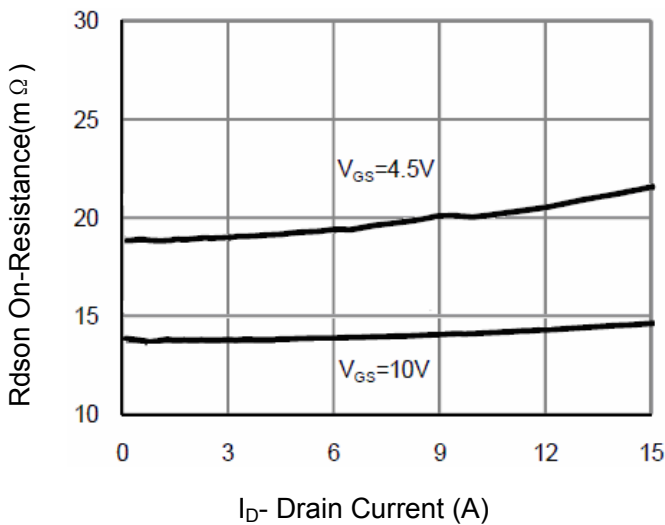


Figure 5 Drain-Source On-Resistance

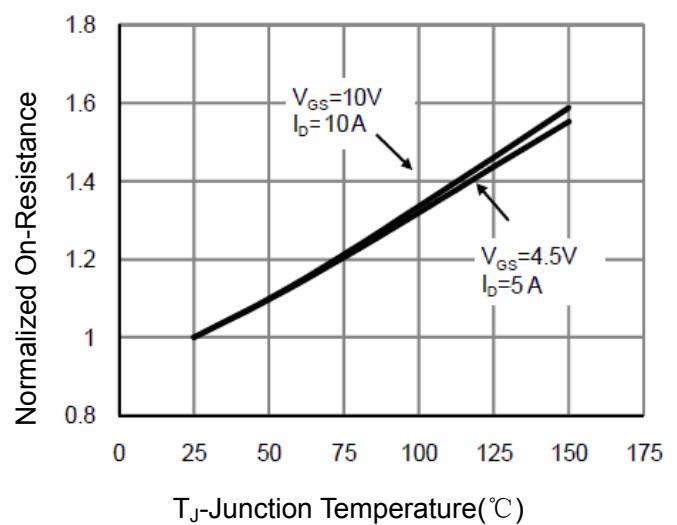
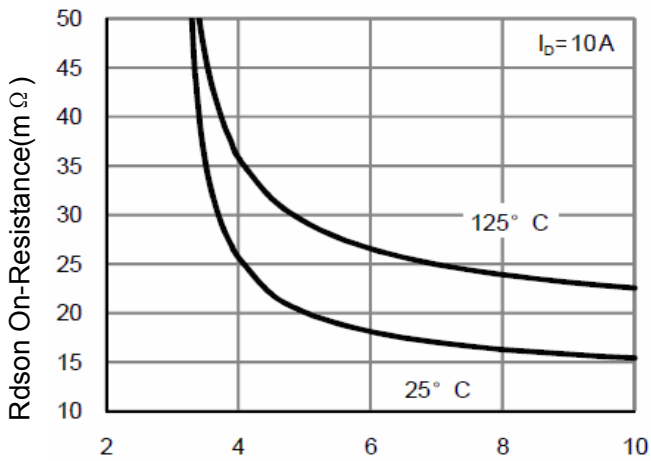
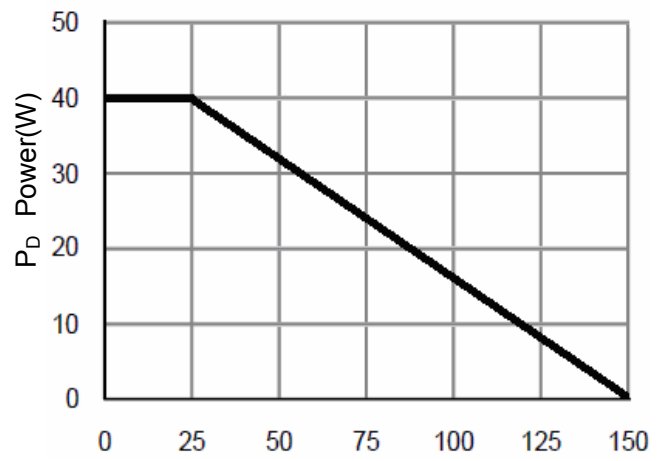


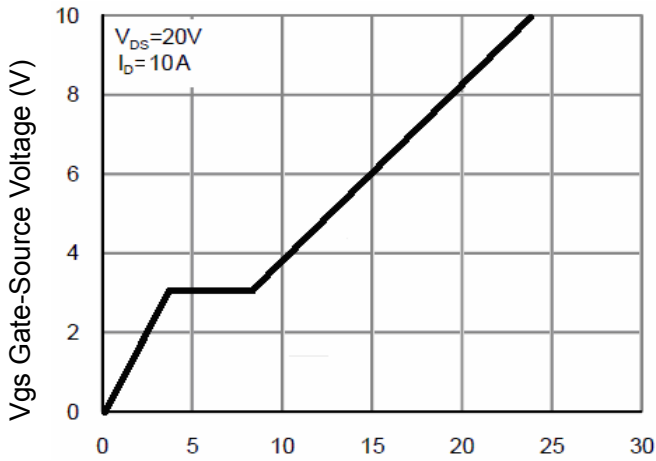
Figure 6 Drain-Source On-Resistance



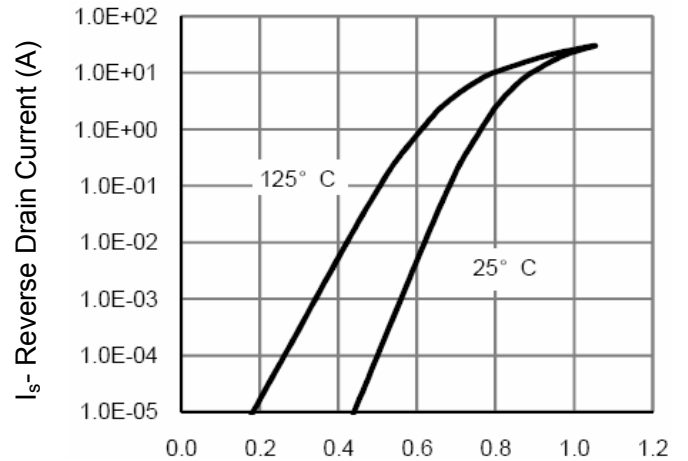
Vgs Gate-Source Voltage (V)
Figure 7 Rdson vs Vgs



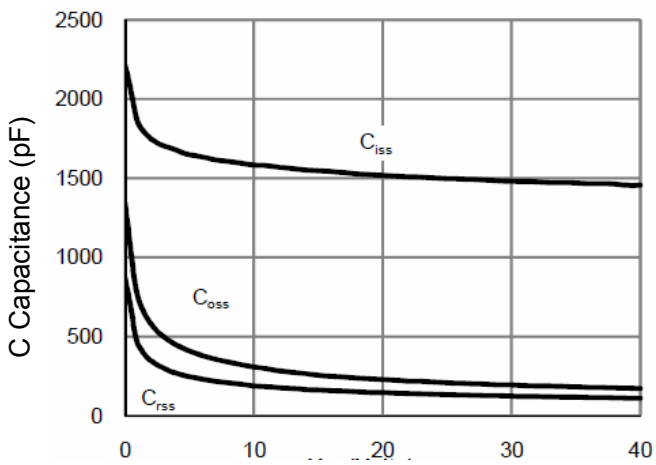
Tj Junction Temperature (°C)
Figure 8 Power Dissipation



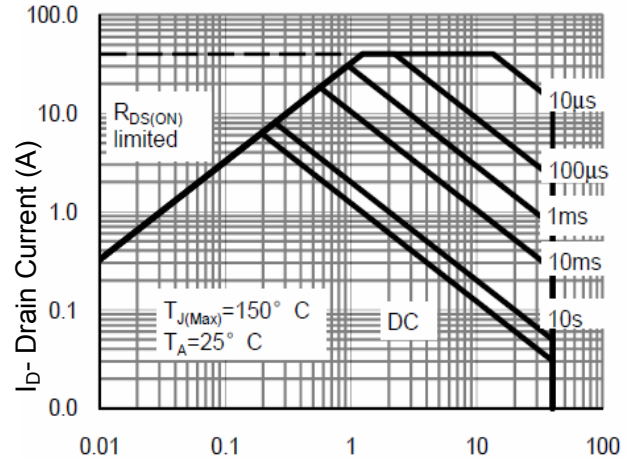
Qg Gate Charge (nC)
Figure 9 Gate Charge



Vds Drain-Source Voltage (V)
Figure 10 Source- Drain Diode Forward



Vds Drain-Source Voltage (V)
Figure 11 Capacitance vs Vds



Vds Drain-Source Voltage (V)
Figure 12 Safe Operation Area

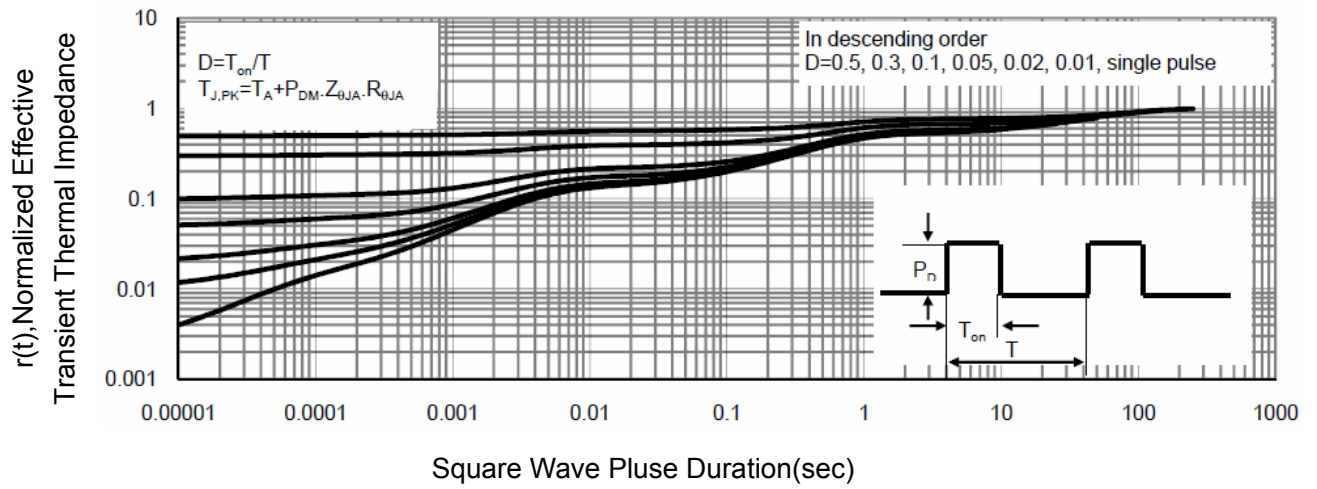


Figure 13 Normalized Maximum Transient Thermal Impedance

P- Channel Typical Electrical and Thermal Characteristics (Curves)

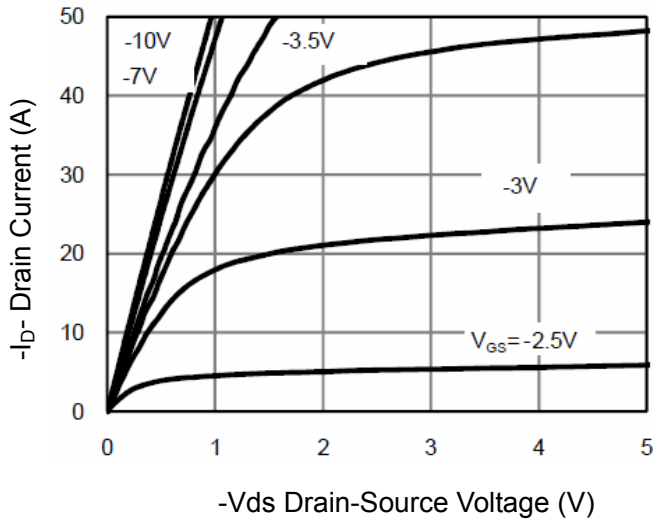


Figure 1 Output Characteristics

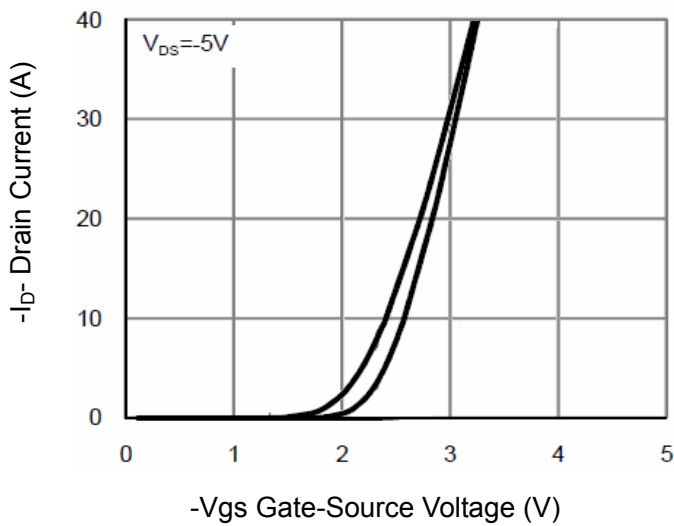


Figure 2 Transfer Characteristics

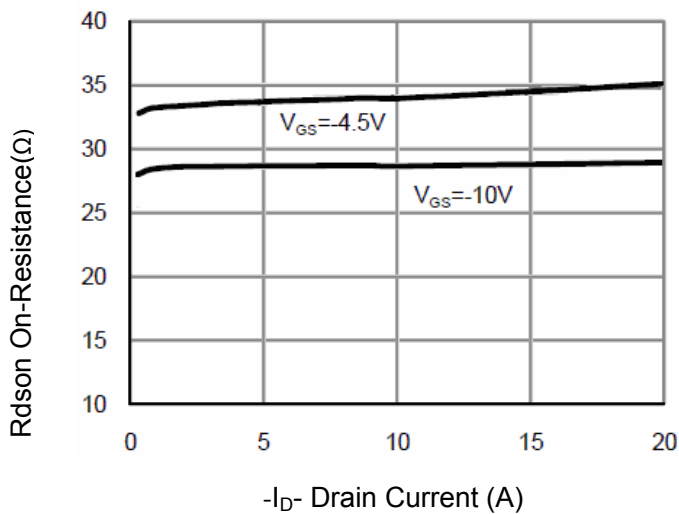


Figure 3 Rdson- Drain Current

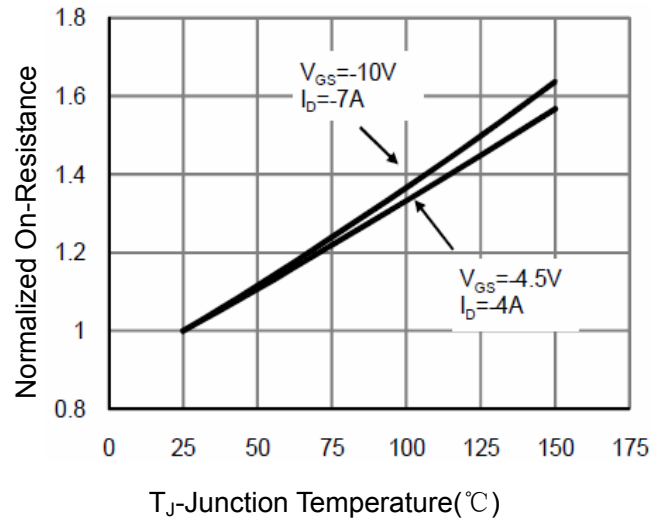


Figure 4 Rdson-Junction Temperature

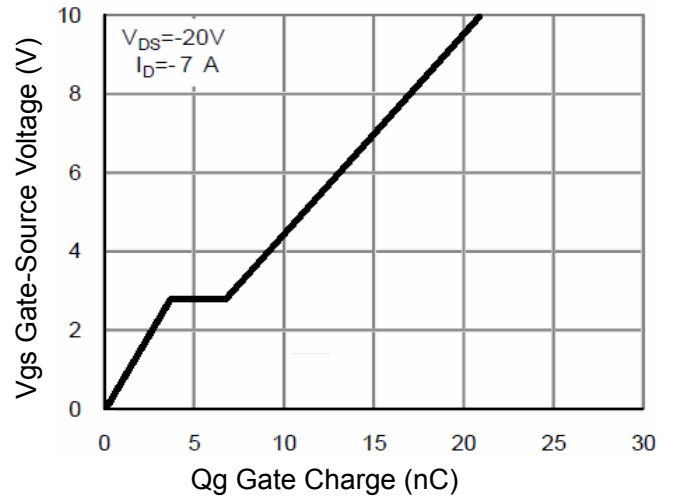


Figure 5 Gate Charge

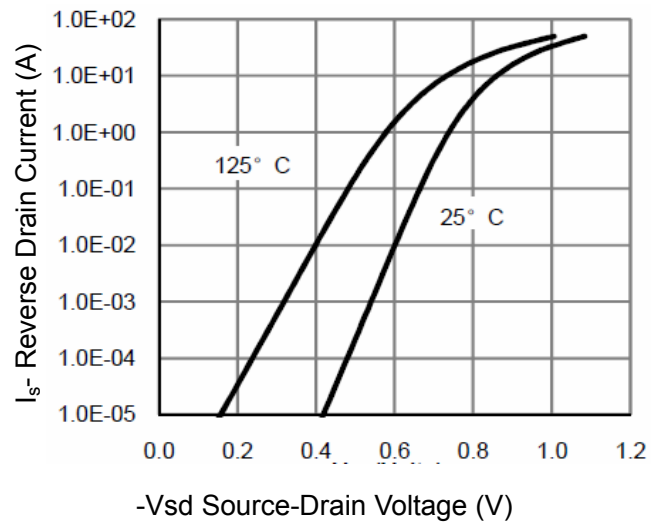
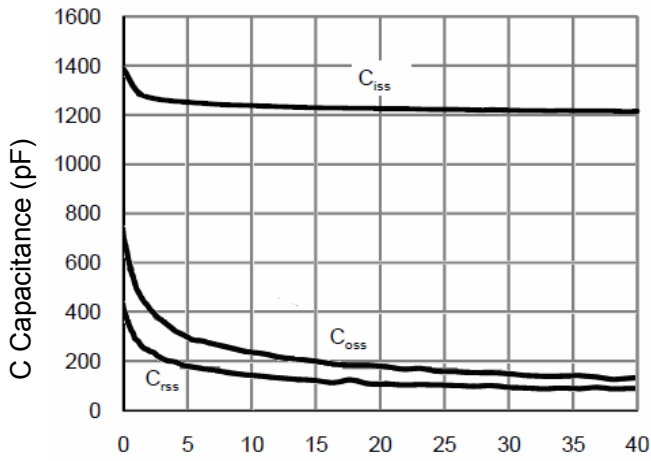
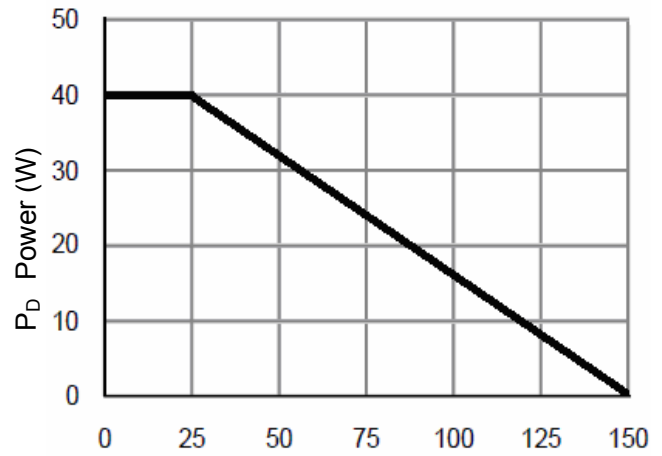


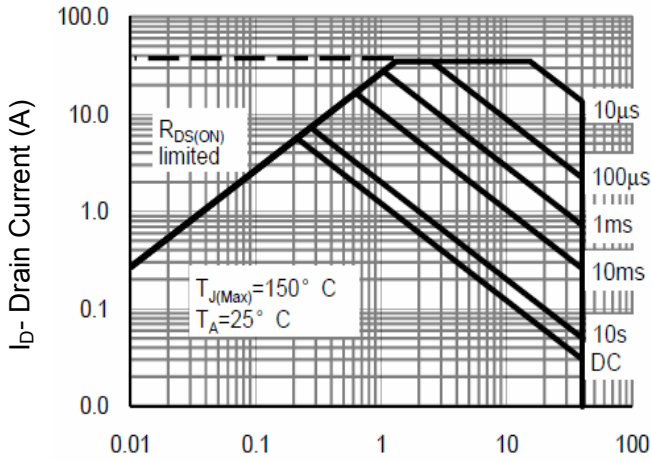
Figure 6 Source- Drain Diode Forward



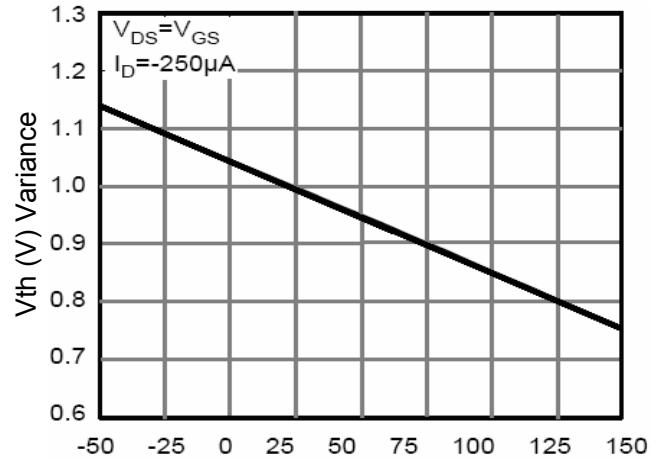
-Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



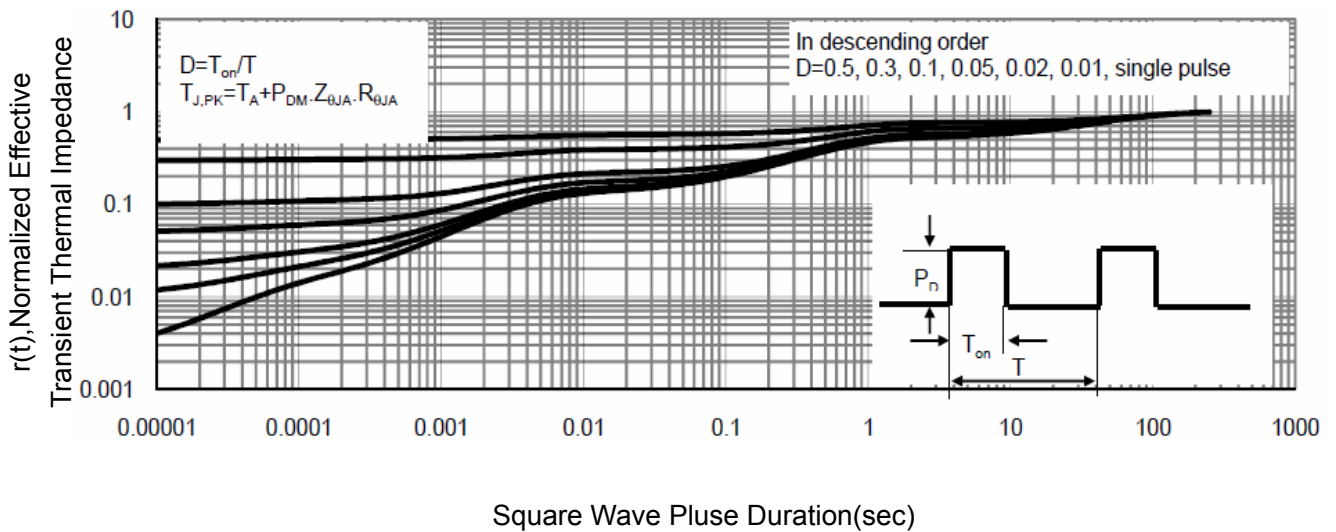
T_J-Junction Temperature(°C)
Figure 9 Power Dissipation



-Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area

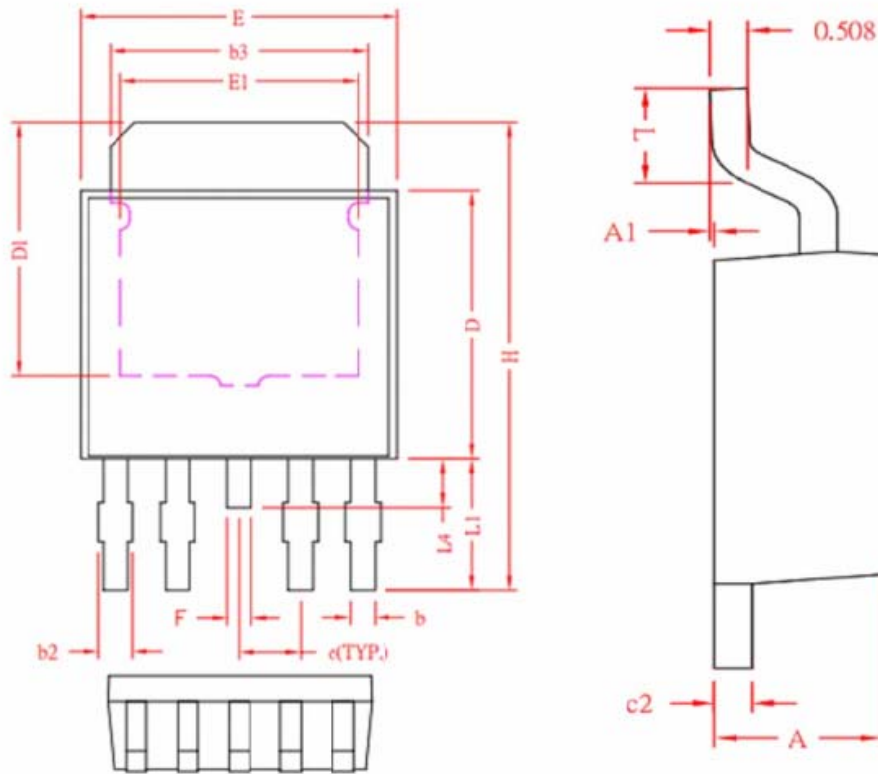


T_J-Junction Temperature(°C)
Figure 10 V_{GS(th)} vs Junction Temperature



Square Wave Pulse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252-4L Package Information



COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0	0.08	0.15
b	0.45	0.53	0.60
b2	0.50	0.65	0.80
b3	5.20	5.35	5.50
c2	0.45	0.50	0.55
D	5.40	5.60	5.80
D1	4.57	-	-
E	6.40	6.60	6.80
E1	3.81	-	-
e	1.27 REF.		
F	0.40	0.50	0.60
H	9.40	9.80	10.20
L	1.40	1.59	1.77
L1	2.40	2.70	3.00
L4	0.80	1.00	1.20

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